A Semiconductor Device Having A Second Level Of Metallization Formed Over A First Level With Minimal Damage To The First Level And Method

ABSTRACT OF THE DISCLOSURE

A semiconductor device having an upper level of metallization interconnected with a lower level of metallization and a method of forming the device is provided. Accordingly, the process of the invention includes capping the lower level of metallization with an thin stop layer having a thickness of less than 300Å and preferably about 100Å such that the etching and ashing processes of removing photoresist and intermediate portions of etch stop layer is accomplished without damage to the lower level metallization.